

Silicon Monolithic Integrated Circuit STRUCTURE

PRODUCT SERIES 7-Channel Switching Regulator Controller for Digital Camera

BD9350MWV TYPE

PIN ASSIGNMENT Fig.1 **BLOCK DIAGRAM** Fig.1 PACKAGE Fig.2 **Functions**

●1.5V minimum input operating

- Supplies power for the internal circuit by using charge-pump circuit which outputs a voltage twice bigger than VBATvoltage. or a equal voltage as VBAT + VIN.
- Contains step-up converter(1ch), step-down converter(2ch), cross converter(1ch), configurable for step-up/step-down converter(1ch), with 32 step brightness controller for step-up converter(1ch).
- Contains 4FETs for the cross converter channe.l
- ●3channels contain transistor for synchronous rectifying action mode.
- ●2channels contain FETs for the step-up converter.
- All channels contain internal compensation between inputs outputs of error amps.
- Contains sequence control circuit for ch1,2 and 4.
- lacktriangle Operating frequency 1.2MHz(CH1 \sim 4), 600kHz(CH5 \sim 7).
- Contains output interception circuit when over load.
- •2 channels have high side switches with soft start function, one channel has PMOS back gate control circuit.
- ●Thermally enhanced UQFN044V6060 package.(6mm x 6mm, 0.4mm pitch)

OAbsolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Power Supply Voltage	VBAT	-0.3~7	V
	VHx1∼4	−0.3~7	V
Dames Inches Vallages	HS67H	−0.3~7	V
Power Input Voltage	VLx6~7	-0.3~20	٧
	VIN	-0.3~7	٧
	IomaxLx1	±12	Α
	IomaxHx2	±1.5	Α
Output Current	IomaxHx3∼4	±12	Α
	IomaxHS6∼7	±12	A
	IomaxLx6∼7	±0.8	Α
Power Dissipation	Pd	0.54 (*1)	W
Operating Temperature	Topr	−25~+85	°C
Storage Temperature	Tstg	−55~+150	°C
Junction Tempareture	Tjmax	+150	°C

(*1) Without external heat sink, the power dissipation reduces by $4.32 \text{mW/}^{\circ}\text{C}~\text{over}~25^{\circ}\text{C}_{\circ}$

ORecommended operating conditions

OCH7 recommended operating conditions

Parameter	Symbol		Unit		
Parameter		MIN	TYP	MAX	Oill
Power Supply Voltage	VBAT	1.5	-	5.5	٧
VREF Pin Connecting Capacitor	CVREF	0.47	1.0	4.7	μF
VREGA Pin Connecting Capacitor	CVREGA	0.47	1.0	4.7	μF
SCP Pin Connecting Capacitor	CSCP	_	-	0.47	μF
C+H to C+L connecting Capacitor	CF	1.0	-	-	μF
[Oscillator]					
Oscillator Frequency	fosc	0.6	12	1.5	MHz
OSC Timing Resistor	RT	47	62	120	kΩ

Parameter	Symbol		Unit		
Parameter		MIN	TYP	MAX	Unit
Fixed H when determine brightness	T(ON)	65X1/fosc	-	-	[S]
Fixed L when OFF	T(OFF)	65X1/fosc	-	-	[S]
Fixed H when setting brightness	T(H)	420	-	10000	[nS]
Fixed L when setting brightness	T(L)	420	-	10000	[nS]
Fixed H when EN start-up	T(EN)	5X1/fosc	-	-	[S]
Fixed L before setting brightness	T(CLR)	5X1/fosc	-	63X1/fosc	[S]
Brightness setting time When start-up	T(SET)	-	-	2048X1/fosc	[S]

Status of this document

The Japanese version of this document is the official specification. Please use the translation version of this document as a reference to expedite understanding of the official version. If these are any uncertainty in translation version of this document, official version takes priority.



OElectrical characteristics (Ta=25°C, VBAT=3V, RT=62k, STB1~6=3V,UPIC7=2.5V)

		9	tandard valu	10			
Parameter	Symbol	MIN	TYP	MAX	Units	Conditions	
Charge Pump Circu							
Output Voltage	Vcpout1	52	5.4	_	٧	Io=1mA,, INV1~7=12V	
(Regulated)	ropouci	02	0.1		•	NON5= -0.2V	
Output Voltage (X2 Step up)	Vcpout2	4.5	4.8	_	٧	Only for internal Current VBAT=25V, INV1~7=12V NON5=-02V	
Output Resistance	Vcpro	-	35	50	Ω	CF=1 μ F, VBAT=25V	
Operating Frequency	fcp	60	75	90	kHz	RT=62kΩ	
Minimum VBAT Voltage	Vst1	1.5	-	_	٧		
[Internal Regulator V	REGA]						
Output Voltage	VREGA	2.4	2.5	2.6	V	Io=5mA	
Prevention Circuit of	f Miss Operati	on by Low v	oltage Input]			
Threshold Voltage	Vstd1	_	2.15	2.30	V	VREGA Monitor	
Hysteresis Width	∠Vstd1	50	100	200	mA		
Short Circuit Protect	ction]	ı		1	1	Г	
Timer start threshold voltage	Vtcinv	0.42	0.48	0.54	V	INV monitor CH4	
SCP Stand by Voltage	Vssc	-	22	170	mV		
SCP Out Source Current	Iscp	2	4	6	μА	Vscp=0.1V	
SCP Threshold Voltage	Vsap	0.9	1.0	1.1	٧		
[Oscillator]							
Frequency							
CH1~4	fosc1	1.0	12	1.4	MHz	RT=62kΩ	
Frequency CH5~7	fosc2	0.5	0.6	0.7	MHz	RT=62kΩ	
Max Duty 1,3,4 (Step Down)	Dmax1d	-	-	100	%	Vsqp=0V (※1)	
Max Duty 1,4(Step Up)	Dmax1u	86	92	96	%		
Max Duty 5,6,7	Dmax2	86	92	96	%		
Max Duty CH2 LX21	Dmax3	-	-	100	%		
Max Duty CH2 LX22	Dmax4	78	84	90	%		
[Error AMP]							
Input Biias Current	IINV	_	0	50	nA	INV1~7, NON5=3.0V	
INV Threshold Voltage1	VINV1	0.79	0.80	0.81	٧	CH1~4	
INV Threshold Voltage2	VINV2	0.99	1.00	1.01	V	CH6, 7V	
INV Threshold Voltage3	VINV3	513	540	567	mV	CH7I	
Base Bias Voltage	/ref for inverte	d Channel 1	1	1	1	I	
CH5 OutputVoltage	VOUT5	-6.09	-6.00	-5.91	V	NON5 resistor12kΩ, 72kΩ (※2)	
Line Regulation	DVLi	_	4.0	12.5	mV	CPOUT=1.5~5.5V	
Output Current		_		120			
When shorted [Soft Start]	los	0.2	1.0	_	mA	Vref=0V	
CH1,24							
Soft Start Time	Tss1,2,4	1.5	2.5	3.5	msec	RT=62kΩ	
CH3 Soft Start Time	Tss3	0.5	1.5	2.5	msec	RT=62kΩ	
CH5 Soft Start Time	Tss5	1.5	2.5	3.5	msec	RT=62kΩ	
CH6 Soft Start Time	Tss6	20	3.0	4.0	msec	RT=62kΩ	
CH7 Soft Start Time	Tss7	4.7	5.7	6.7	msec	RT=62kΩ	
SOIL GUILL TILLE							

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Parameter		Symbol	Standard value Min TYP		MAX	Units	Conditions
[Output Driver]							
CH1 Highside SW		RON1P	_	160	380	mΩ	HX1=3V,
ON Resistan		TOM		100	300	11135	CPOUT=5.4V
CH1 Lowside		RON1N	_	130	180	mΩ	CPOUT=5.4V
ON Resistan							
Highside SW	'	RON21P	_	160	240	mΩ	HX2=3.0V,
ON Resistan	ce						CPOUT=5.4V
CH2 LX21Pir	n						
Lowside SW		RON21N	_	130	200	mΩ	CPOUT=5.4V
ON Resistan							
CH2 LX22Pir Highside SW	1	RON22P		180	280	mΩ	VOUT2=5.0V
ON Resistan	ne	RUNZZP	_	180	280	m32	VOU12=3.0V
CH2 LX22Pir							
Lowside SW	•	RON22N	_	130	200	mΩ	CPOUT=5.4V
ON Resista	nce						
CH3 Highside		RON3P	_	160	260	mΩ	HX3=3.0V,
ON Resistan		1101101		100	200	11126	CPOUT=5.4V
CH3 Lowside		RON3N	_	130	200	mΩ	CPOUT=5.4V
ON Resistan		-					
ON Resistan		RON4P	_	280	380	mΩ	HX4=5.0V
CH4 Lowside							
ON Resistan	ce	RON4N	_	130	200	mΩ	CPOUT=5.4V
CH6 NMOS	SW	RON6N	_	500	800	mO	CPOUT=5.4V
ON Resistan	ce	RONON	_	300	800	mΩ	
CH6,7 Load S		RON67P	_	200	300	mΩ	HS67H=3.0V
ON Resistan	ce						CPOUT=5.4V
	CH5 Driver Output Voltage H		PVCC5	PVCC5		.,	IOUT5=50mA, NON5=0.2V.
Output voita			-1.5	-1.0	_	V	PVCC5=3V
CH5 Driver						.,	IOUT5=50mA,
Output Volta	ge L	Vout5L	_	0.5	1.0	V	NON5=0.2V
[Switch to co	onfigure step up	/down]					
UDSEL4	Step down	VUDDO	OPOUT 207	_	CPOUT	V	
Control			×0.7		CPOUT		
Voltage	Step up	VUDUP	0	ı	×0.3	V	
[STB1~6]			,		,	,	
STB control	Active	VSTBH1	1.5	-	5.5	V	
Voltage	Non Active	VSTBL1	-0.3	_	0.3	V	
Pull down Re	sistance	RSTB1	250	400	700	kΩ	
[UPIC7]			1		1		T.
UPIC7 control	Active	VUPIH	2.05	_	4.0	V	
Voltage	Non Active	VUPIL	0		0.4	V	
[Circuit Curr							
	VBAT terminal	ISTB1	_	_	5	μΑ	
0	HS67H	ICTEO			-	,	
Stand-by	terminal	ISTB2	_	_	5	μА	
Current	HX terminal	ISTB3	_	_	5	μА	Step -down UDSEL4=CPOUT
	LX terminal	ISTB4	_	_	5	μΑ	Step-up UDSEL4=0V
Circuit Current1					,	,,,,	
(VBAT current		In : 1	_	70	110		INV1~7=1.2V,
when voltage supplied		Icc1	_	7.0	11.0	mA	NON5=-0.2V, VBAT=3.0V
for the terminal)							
Circuit Curre							INV1~7=12V,
(CPOUT cur		Icc2	-	3.0	5.0	mA	NON5=-0.2V, CPOUT=5.4V
when voltage supplied							C+H, C+L=OPEN
for the termin	iai/						1

 $^{(\}frac{1}{2})$ The protective circuit start working when circuit is operated by 100% duty.

So it is possible to use only for transition time shorter than charge time for SCP.

⁽ $\mbox{\ensuremath{\%}}\mbox{\ensuremath{2}}\mbox{\ensuremath{N}}\mbox{\ensuremath{N}}\mbox{\ensuremath{2}}\mbox{\ensuremath{N}}\mbox{\ensuremath{2}}\mbox{\ensuremath{2}}\mbox{\ensuremath{N}}\mbox{\ensuremath{2}}\mbox{$

⁽ $\frak{3}$)UPIC7 is not connected pull-down resistor. UPIC7 must input H or L level voltage when CH1 \sim 6 is active.

This product is not designed for normal operation with in a radioactive environment



OPin Assignment •Block Diagram

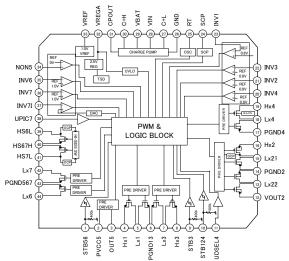


Fig. 1

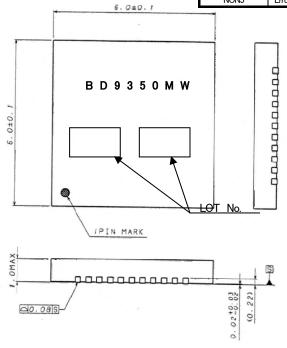
OPin Description

Pin Name	Description			
VBAT	Input for battery voltage			
VIN	Returning voltage			
VIIV	from output terminal			
CPOUT	Output terminal			
CFOOT	for Charge Pump			
GND	Ground terminal			
C+H	Terminal for connecting flying			
Cill	capacitor for Charge Pump(H side)			
C+I	Terminal for connecting flying			
OiL	capacitor for Charge Pump(L side)			
PGND13,2,4,567	Ground terminal for internal FET			
VREGA	VREGA output			
VREF	CH5 base bias voltage			
PVCC5	CH5 PMOS VCC input for driver			

Pin Name	Description			
OUT5	Terminal for connecting gate of CH5 PMOS			
Hx1,3,4	Input terminal for synchronous High side switch, Power supply for Pch Driver			
Lx1,3467	Terminal for connecting inductors			
H⁄2	Power supply for channel 2			
Lx21	Terminal for connecting inductor for CH2 input			
Lx22	Terminal for connecting inductor for CH2 output			
VOUT2	CH2 output voltage			
HS67H	Power supply for internal load switch			
HS6L,HS7L	Output terminal for internal load switch			
INV1,2,3,4,6,7	Error AMP inverted input			
NON5	Error AMP non-inverted input			

Pin Name	Description
INV7I	Error AMP inverted input
RT	For connecting a resistor to set the OSC frequency
SCP	For connecting a capacitor to set up the delay time of the SCP
UDSEL4	Step-up/down switching mode selection(H: step-down, L:step-up)
STB124,3,56	ON/OFF switch H: operating over 1.5V
UPIC7	ON/OFF switch for CH7 brightness control

OPackage



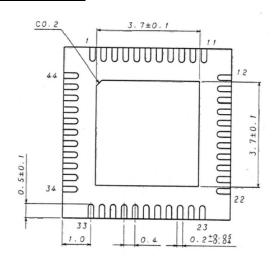


Fig. 2



OOperation Notes

Absolute maximum ratings

This product is produced with strict quality control. However, the IC may be destroyed if operated beyond its absolute maximum ratings. If the device is destroyed by exceeding the recommended maximum ratings, the failure mode will be difficult to determine. (E.g. short mode, open mode) Therefore, physical protection counter-measures (like fuse) should be implemented when operating conditions beyond the absolute maximum ratings anticipated.

2.) GND potential

Make sure GND is connected at lowest potential. All pins except NON5, must not have voltage below GND. Also, NON5 pin must not have voltage below - 0.3V on start up.

3.) Setting of heat

Make sure that power dissipation does not exceed maximum ratings.

4.) Pin short and mistake fitting

Avoid placing the IC near hot part of the PCB. This may cause damage to IC. Also make sure that the output-to-output and output to GND condition will not happen because this may damage the IC.

5.) Actions in strong magnetic field

Exposing the IC within a strong magnetic field area may cause malfunction.

6.) Mutual impedance

Use short and wide wiring tracks for the main supply and ground to keep the mutual impedance as small as possible. Use inductor and capacitor network to keep the ripple voltage minimum.

7.) Voltage of STB pin

The threshold voltages of STB pin are 0.3V and 1.5V. STB state is set below 0.3V while action state is set beyond 1.5V. The region between 0.3V and 1.5V is not recommended and may cause improper operation.

The rise and fall time must be under 10msec. In case to put capacitor to STB pin, it is recommended to use under 0.01 μ F.

8.) Thermal shutdown circuit (TSD circuit)

The IC incorporates a built-in thermal shutdown circuit (TSD circuit). The thermal shutdown circuit (TSD circuit) is designed only to shut the IC off to prevent runaway thermal operation. It is not designed to protect the IC or guarantee its operation. Do not continue to use the IC after operating this circuit or use the IC in an environment where the operation of this circuit is assumed.

9.) Rush current at the time of power supply injection.

An IC which has plural power supplies, or CMOS IC could have momentary rush current at the time of power supply injection. Please take care about power supply coupling capacity and width of power Supply and GND pattern wiring.

1 O.)IC Terminal Input

This IC is a monolithic IC that has a P- board and P+ isolation for the purpose of keeping distance between elements. A P-N junction is formed between the P-layer and the N-layer of each element, and various types of parasitic elements are then formed. For example, an application where a resistor and a transistor are connected to a terminal (shown in Fig.15):

- OWhen GND > (terminal A) at the resistor and GND > (terminal B) at the transistor (NPN), the P-N junction operates as a parasitic diode.
- When GND > (terminal B) at the transistor (NPN), a parasitic NPN transistor operates as a result of the NHayers of other elements in the proximity of the aforementioned parasitic diode.

Parasitic elements are structurally inevitable in the IC due to electric potential relationships. The operation of parasitic elements Induces the interference of circuit operations, causing malfunctions and possibly the destruction of the IC. Please be careful not to use the IC in a way that would cause parasitic elements to operate. For example, by applying a voltage that is lower than the GND (P-board) to the input terminal.

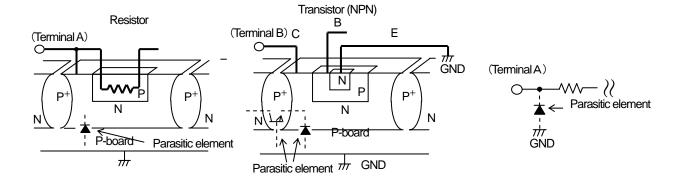


Fig - 3 Simplified structure of a Bipolar IC

Notes

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